

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	257/79 and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/04/01 13:44
L2	6	257/79 and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) same gate near electrode same (source or drain)	USPAT; JPO	OR	ON	2005/04/01 14:29
L3	1215	349/139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:18
L4	899	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:28
L5	528	349/152	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:37
L6	7213	(ITO or indium near tin near oxide) with (residue or remnant or left near over or ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
L7	10	(ITO or indium near tin near oxide) with (residue or remnant or left near over) with (ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:42
L8	6749	(ITO or indium near tin near oxide) with (ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:47

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L9	3375	(ITO or indium near tin near oxide) with (ring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:43
L10	221	(ITO or indium near tin near oxide) with (ring) with (wir\$3 or film or layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:44
L11	212	(ITO or indium near tin near oxide) with (ring) with (enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
L12	3608	(ITO or indium near tin near oxide) with (enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
L13	2	(ITO or indium near tin near oxide) with (residue or remnant or left near over) with (enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:05
L14	4646	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:15
L15	174	257/449	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:28
L16	172	257/749	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:37

L17	5	257/e51.005	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:44
L18	1214	257/79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:56
L19	3773	257/347	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:08
L20	1825	257/350	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:18
L21	269	257/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:33
L22	1	257/E33.064	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
L23	0	257/E31.126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
L24	4	257/E29.151	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34

L25	0	257/E23.157	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:35
L26	132	438/609	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:36
L27	2549	174/255	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:37
L28	1044	174/256	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:45
L29	807	174/257	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 18:02
L30	938	174/258	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 18:02
S1	640	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide)	USPAT	OR	ON	2005/03/31 19:21
S2	45	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide) near electrode and (ITO or indium near tin near oxide) near (layer or film or structure)	USPAT	OR	ON	2005/03/31 19:36

S3	0	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide) near gate and (ITO or indium near tin near oxide) near (source or drain)	USPAT	OR	ON	2005/03/31 19:37
S4	0	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) near gate near electrode and (ITO or indium near tin near oxide) near (source or drain)	USPAT	OR	ON	2005/03/31 19:37
S5	82	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S6	281	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) same gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S7	259	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S8	259	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S9	278	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/04/01 13:43
S10	177	S8 not S5	USPAT; JPO	OR	ON	2005/03/31 20:17

S11	94	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/03/31 20:54
S12	12	S11 not S5	USPAT; JPO	OR	ON	2005/03/31 20:55

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